

Silicon NPN Power Transistors

2SC2773

DESCRIPTION

- With MT-200 package
- High current capability

APPLICATIONS

- For audio power amplifier and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

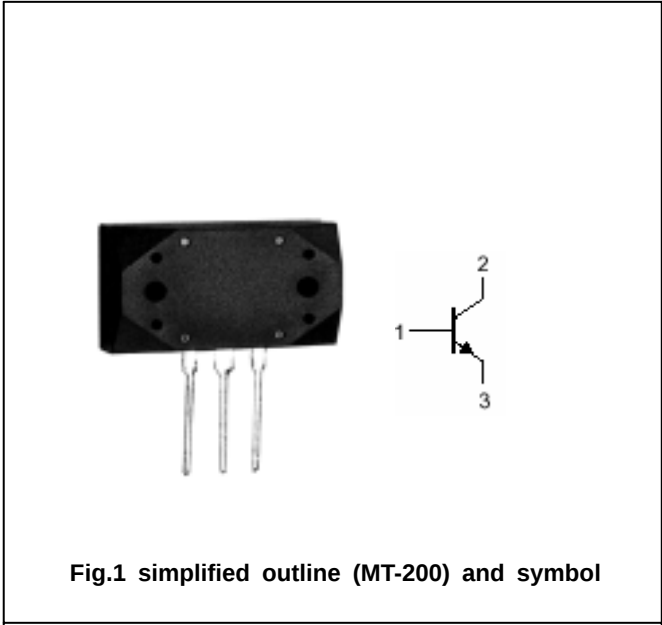


Fig.1 simplified outline (MT-200) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	200	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25	150	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

Silicon NPN Power Transistors**2SC2773****CHARACTERISTICS****T_j=25** unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA$; $I_B=0$	200			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA$; $I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=10A$; $I_B=1A$			3.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=200V$; $I_E=0$			100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V$; $I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=5A$; $V_{CE}=4V$	50		180	
f_T	Transition frequency	$I_C=0.5A$; $V_{CE}=12V$		20		MHz
C_{OB}	Output capacitance	$I_E=0$; $V_{CB}=10V$; $f=1MHz$		250		pF

◆ **h_{FE} classifications**

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

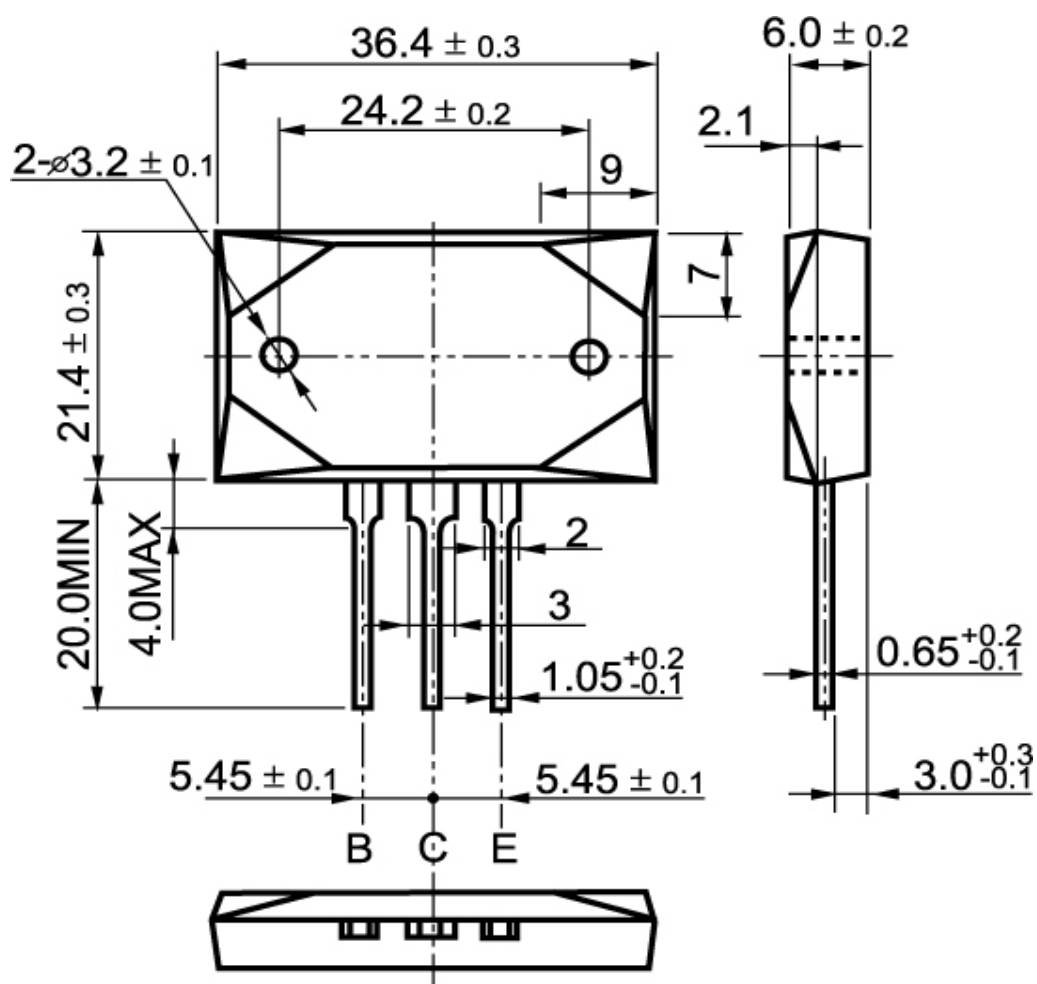


Fig.2 Outline dimensions